DIC L2: Introduction (2)

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1.3. MOS transistors (6)

- PMOS
  - Similar, but doping and voltages are reversed.
  - Body is tied to V_{DD}.
  - V_{GS} is negative.

Metal (Polysilicon gates are gone.)

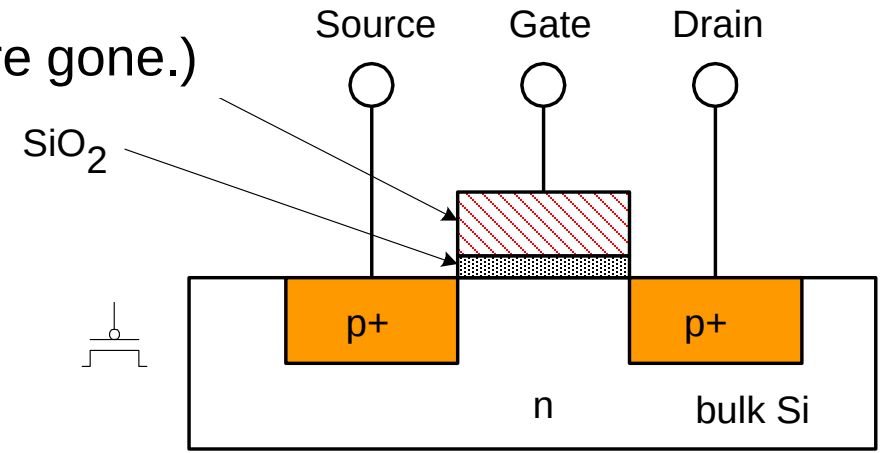
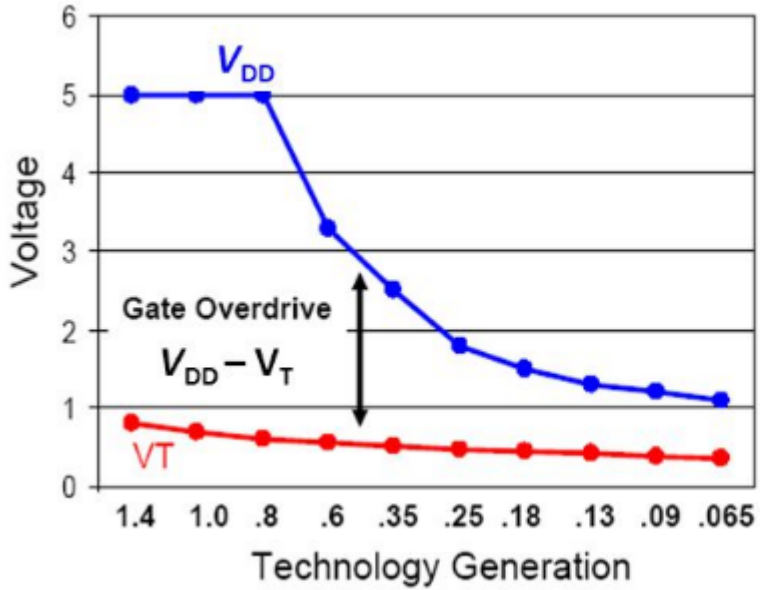


Fig. 1.9(b)

1.3. MOS transistors (7)

- Power supply voltage
  - In 1980's, V_{DD} was 5 V.
- IEDM(or VLSI) papers
  - 130nm: 2000
  - 90nm: 2003
  - 65nm: 2004
  - 45nm: 2007
  - 32nm: 2008
  - 22nm: 2012
  - 14nm (or 16nm): 2014



Source: P. Packan (Intel), 2007 IEDM Short Course

1.3. MOS transistors (8)

- Transistors as switches
  - V_G controls path from source to drain.

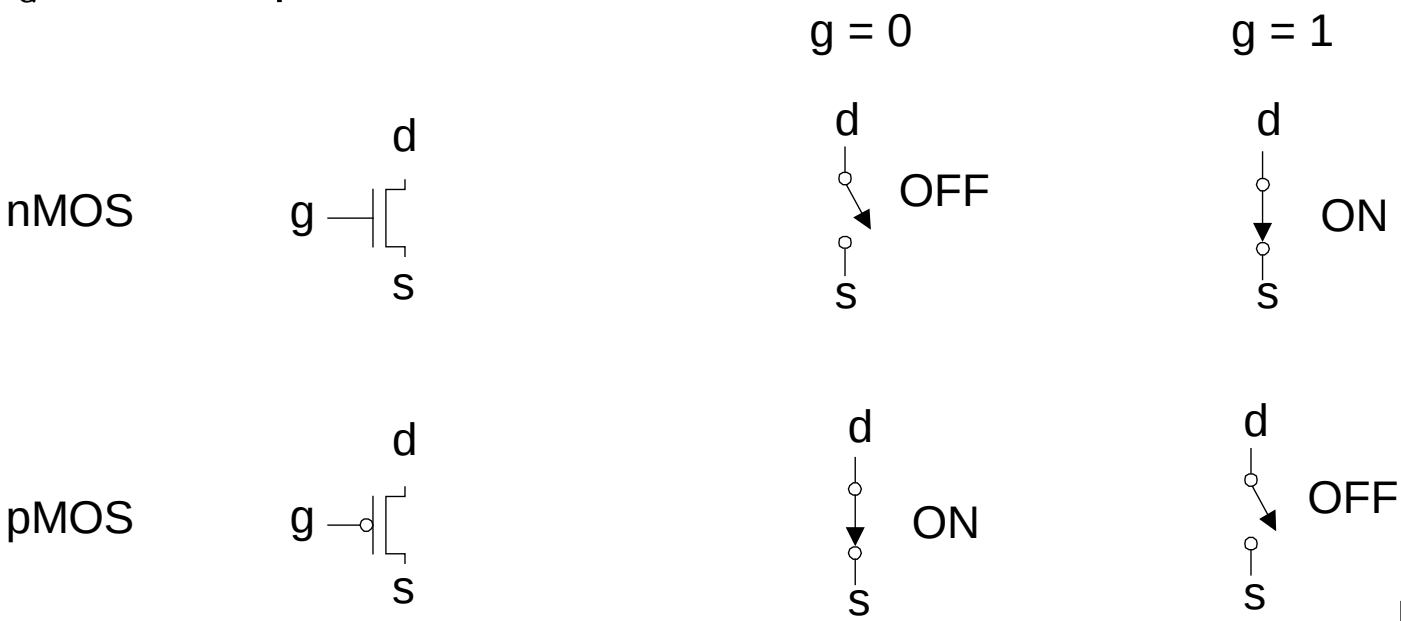


Fig. 1.10

1.4. CMOS logic (1)

- CMOS inverter
  - When the input A is 0,

    the NMOS transistor is OFF and

    the PMOS transistor is ON.
  - Thus, the output Y is pulled up to 1.

A	$Y = NOT\ A$
0	1
1	0

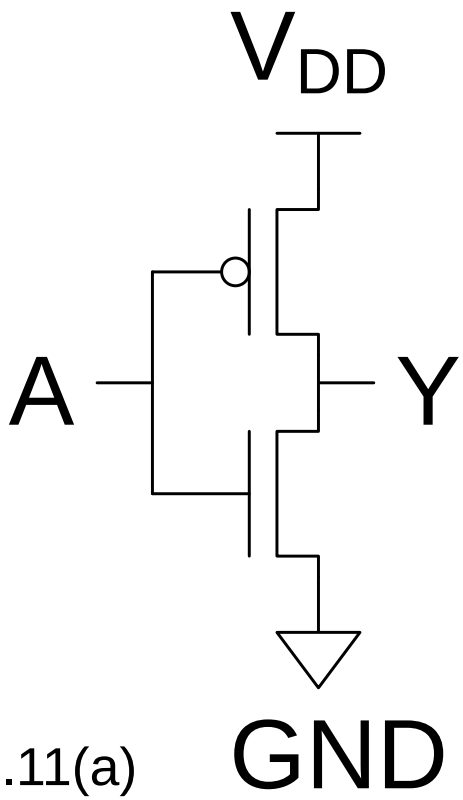
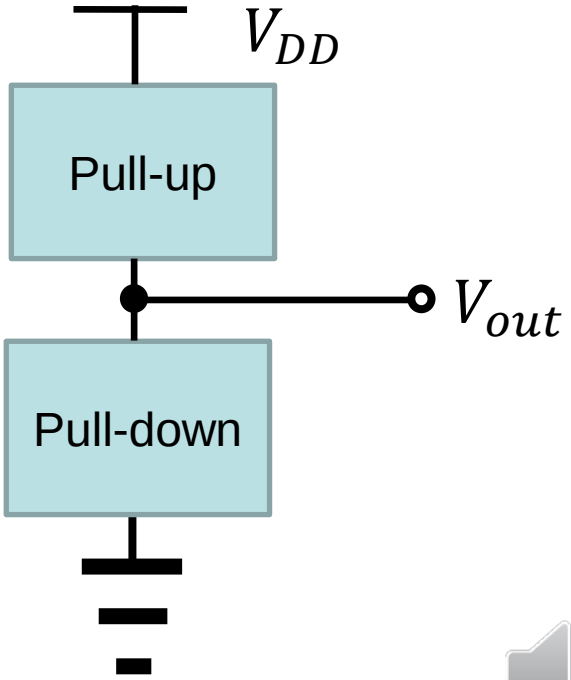


Fig. 1.11(a)

1.4. CMOS logic (2)

- Complementary CMOS gates
- Pull-down and pull-up networks
  - NMOS pull-down
  - PMOS pull-up



	Pull-up OFF	Pull-up ON
Pull-down OFF	Z	1
Pull-down ON	0	Crowbarred (X)